

a first metal layer formed on said electrode layer formed on said surface layer, a second metal layer formed on said first metal layer, and a third metal layer formed on said second metal layer; and

a protective film over said third metal layer, said protective film leaving exposed a central portion of said third metal layer; said electrode layer being capable of passing an emitted light;

said electrode pad being capable of supplying a current to said electrode layer; and

wherein said second metal layer is made of gold (Au), said first metal layer comprises a material that has an ionization potential lower than gold (Au), and said third metal layer comprises aluminum (Al) that has an adhesiveness to said protection film which is stronger than gold (Au).

6. (Twice Amended) The light-emitting semiconductor device according to claim 1, wherein said electrode layer has a multi-layer structure having at least a first electrode layer formed on said surface layer and a second electrode layer formed on said first electrode layer, wherein said first electrode layer comprises material having an ionization potential that is lower than that of said second electrode layer, said material of said second electrode layer, has an ohmic characteristic to said surface layer better than that of said first electrode layer, and said material of said second electrode layer being distributed more deeply into said surface layer than that of said first electrode layer by heat treatment.

12. (Twice Amended) A light-emitting semiconductor device having a Group III nitride compound semiconductor comprising:

a surface layer made of p-type semiconductor;

a multi-layered electrode layer comprising a first electrode layer formed on said surface layer and a second electrode layer formed on said first electrode layer;

an electrode pad covering a portion of said second electrode layer and leaving another portion of said second electrode layer uncovered; and

wherein said first electrode layer comprises a material which has an ionization potential lower than that of said second electrode layer, said second electrode layer comprises a material which has an ohmic characteristic to said semiconductor better than that of said first electrode layer, and the portion of said material of said second electrode layer which is uncovered by said electrode pad is distributed more deeply into said surface layer than that of said first electrode layer by heat treatment in atmosphere comprising oxygen and provides a contact resistance between said electrode layer and said surface layer lower than said portion covered with said electrode pad.

20. (Twice Amended) The light-emitting semiconductor device according to claim 6, wherein materials of said second electrode layer do not permeate into said first electrode layer directly under said electrode pad, which enables the interface between said electrode layer and said surface layer directly under said electrode pad to have a large resistivity and not have electric current pass therethrough.

Please add the following new claim 27-31:

27. (New) The light-emitting semiconductor device according to claim 12, wherein said atmosphere further includes nitrogen.

28. (New) The light-emitting semiconductor device according to claim 12, wherein atoms of said material of said second electrode layer form an alloy with semiconductor atoms which constitute said surface layer.

29. (New) The light-emitting semiconductor device according to claim 12, wherein said material of said first electrode layer is treated by said heat treatment to form a metal oxide.

30. (New) The light-emitting semiconductor device according to claim 14, wherein said gold (Au) forms an alloy with semiconductor atoms which constitute said surface layer.

31. (New) The light-emitting semiconductor device according to claim 14, wherein said nickel (Ni) is treated by said heat treatment to form nickel oxide.